

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1-25 (Cancelled).

Claim 26 (New): Energy storage device comprising at least one anode, a dielectric and a cathode, in which the elements are coated in part at least by a protective layer formed of a metal or metal alloy having a sufficient thermomechanical resistance to absorb thermomechanical deformations without causing fissures to appear, the metal or the metal alloy having an expansion coefficient less than $6.10^{-6}^{\circ}\text{C}^{-1}$.

Claim 27 (New): Device according to claim 26, the protective layer being formed of a metal chosen among the group W, Ta, Mo, and Zr.

Claim 28 (New): Device according to claim 26, the protective layer being formed of a nitrated alloy chosen among the group WN_x , TaN_x , MoN_x , ZrN_x , TiN_x , and AlN_x , where $x < 1$.

Claim 29 (New): Device according to claim 26, comprising at least one other protective layer formed of a metal or metal alloy having a sufficient thermomechanical resistance to absorb thermomechanical deformations without causing fissures to appear.

Claim 30 (New): Device according to claim 29, wherein another protective layer is formed of a metal having a Vickers hardness less than 50.

Claim 31 (New): Device according to claim 30, wherein the metal is chosen among the group Pd, Pt, and Au.

Claim 32 (New): Device according to claim 26, further comprising an electrically insulating layer.

Claim 33 (New): Device according to claim 32, wherein the insulating layer is located between the elements of the device and the metallic protection layer(s).

Claim 34 (New) Device according to claim 32, wherein the insulating layer is an oxide.

Claim 35 (New): Device according to claim 34, wherein the oxide is chosen among the oxides of Mg, Ca, Be, Ce, Si, Al, Ta and La.

Claim 36 (New): Device according to claim 32, wherein the insulating layer is a sulphide.

Claim 37 (New): Device according to claim 32, wherein the insulating layer is a nitride.

Claim 38 (New): Device according to claim 37, wherein the nitride is chosen among Si_3N_4 and BN.

Claim 39 (New): Device according to claim 32, wherein the insulating layer is a carbide.

Claim 40 (New): Device according to claim 39, wherein the carbide is chosen among SiC, B_4C , and WC.

Claim 41 (New): Device according to claim 26, wherein the elements are encapsulated in the protecting and/or insulating layer(s).

Claim 42 (New): Method for protecting an energy storage device comprising the coating of a part at least of the device by a protective layer formed of a metal or metal alloy having a sufficient thermomechanical resistance to absorb thermomechanical deformations without causing fissures to appear, the metal or the metal alloy having an expansion coefficient less than 6.10^{-6}C^{-1} .

Claim 43 (New): Method according to claim 42, comprising the coating of a part at least of the device by a protective layer formed of a metal having a Vickers hardness less than 50.

Claim 44 (New): Method according to claim 42, where the coating(s) are formed by physical vapour deposition or evaporation.

Claim 45 (New): Method according to claim 42, comprising, prior to the coating(s) by metallic layer(s), the step of coating by an electrically insulating layer.

Claim 46 (New): Method according to claim 45, in which the insulating layer is a ceramic chosen among ZnS, Si₃N₄, BN, SiC, B₄C, WC, MgAl₂O₄ and the oxides of Mg, Ca, Be, Ce, La, Si, Al or Ta.

Claim 47 (New): Method according to claim 45, wherein the coating by an insulating layer is carried out by physical vapour deposition, radiofrequency sputtering or ion beam sputtering.

Claim 48 (New): Method according to claim 45, comprising, prior to the coating by the insulating layer, a step of pre-encapsulation.

Claim 49 (New): Method according to claim 48, comprising the elimination of the pre-encapsulation layer before the coating by the insulating layer.

Claim 50 (New): Method for protecting a microbattery comprising the encapsulation of the microbattery by the method according to claim 42.